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- (71) **Applicant (for all designated States except US):** **INTEL CORPORATION** [US/US]; 2200 Mission College Boulevard, MS: RNB-4-150, Santa Clara, California 95052 (US).
- (72) **Inventors; and**
- (75) **Inventors/Applicants (for US only):** **CHU-KUNG, Benjamin** [US/US]; 2755 Nw John Olsen Ave, Apt #f69, Hillsboro, Oregon 97124 (US). **DEWEY, Gilbert** [US/US]; 920 Se 58th Ave, Hillsboro, Oregon 97123 (US). **RADOSAVLJEVIC, Marko** [US/US]; 4129 Nw Chaparral Terr, Beaverton, Oregon 97006 (US). **MUKHERJEE,**

Niloy [IN/US]; 7732 Sw Carrollon Drive, Beaverton, Oregon 97007 (US).

- (74) **Agents:** **WINKLE, Robert** et al.; Winkle PLLC, c/o CPA GLOBAL, P.O. Box 52050, Minneapolis, Minnesota 55402 (US).

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[Continued on next page]

- (54) **Title:** TUNNEL FIELD EFFECT TRANSISTOR

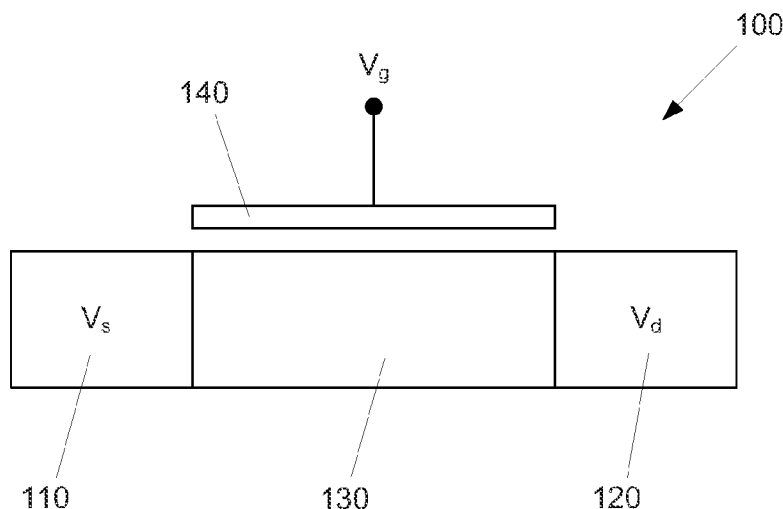


FIG. 1a (prior art)

(57) **Abstract:** The present disclosure relates to the field of microelectronic transistor fabrication and, more particularly, to the fabrication of a tunnel field effect transistor having an improved on-current level without a corresponding increasing the off-current level, achieved by the addition of a transition layer between a source and an intrinsic channel of the tunnel field effect transistor.



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